1N914WT

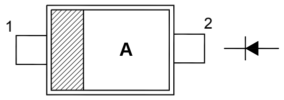
Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**A**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current Pulse Width = 1 s Pulse Width = 1 µs	I_{FSM}	0.5 1	A
Power Dissipation	P_{tot}	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Electrical Characteristics (T_a = 25 °C)

Parameter	Symbol	Min.	Max.	Unit
Breakdown Voltage at I_R = 5 µA at I_R = 100 µA	V_R	75 100	- -	V V
Forward Voltage at I_F = 10 mA	V_F	-	1	V
Reverse Current at V_R = 20 V at V_R = 75 V	I_R	- -	25 5	nA µA
Diode Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_{rr} = 0.1 X I_R, I_F = I_R = 10 mA, R_L = 100 Ω	t_{rr}	-	4	ns

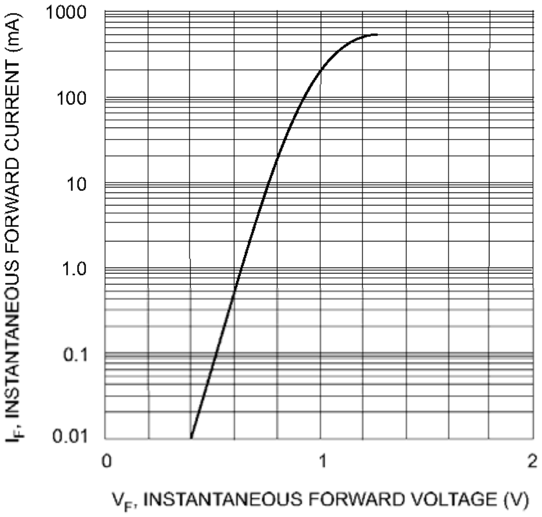


Fig. 1 Forward Characteristics

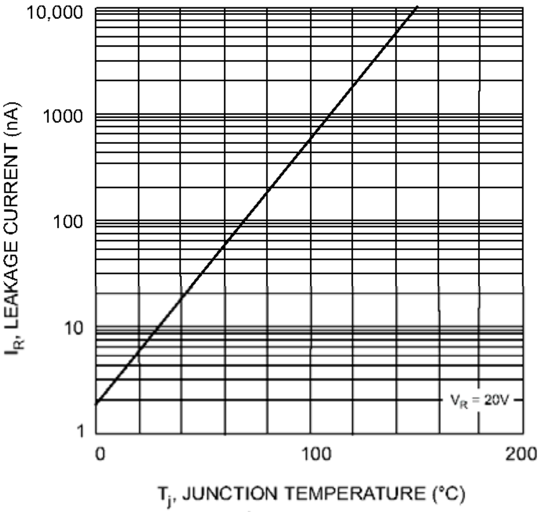
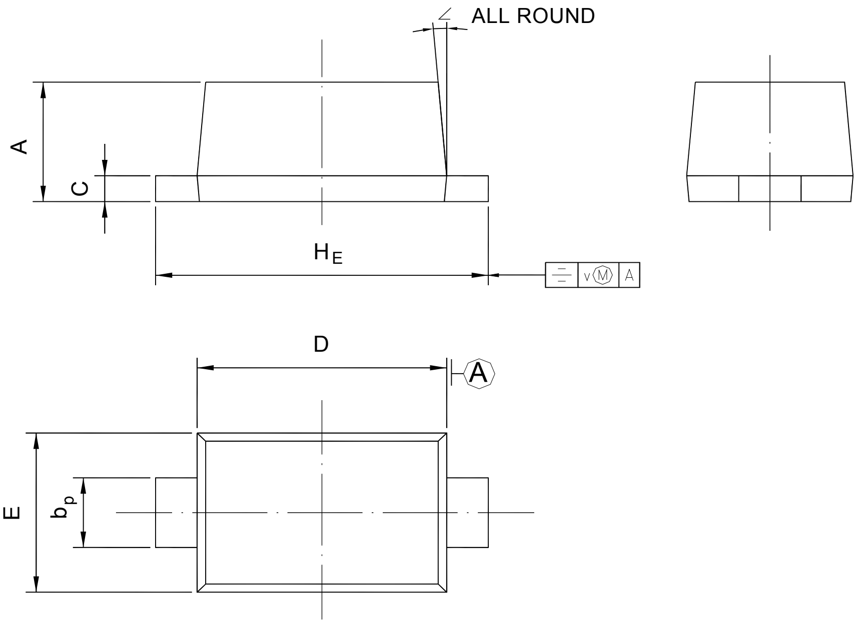


Fig. 2 Leakage Current vs Junction Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°